优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码　　企业QQ二维码

Description

This bipolar junction transistor (BJT) is designed to meet the stringent requirements of automotive applications.

Features

- BV_{CEO} > -60V
- I_C = -6A Continuous Collector Current
- Low Saturation Voltage $V_{CE(sat)}$ < -95mV @ -1A
- $R_{CE(sat)}$ = 40mΩ for a low Equivalent On-Resistance
- h_{FE} Specified up to -10A for a High Current Gain Hold-Up

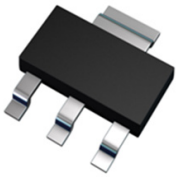
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.112 grams (Approximate)

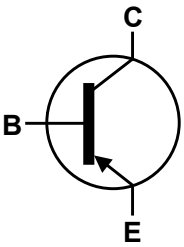
Applications

- Motor Driving
- DC-DC Modules
- Backlight Inverters
- Actuator, Relay and Solenoid Drivers

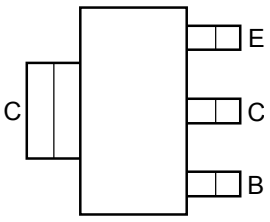
SOT223



Top View



Device Symbol



Top View
Pin-Out

Absolute Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	I_C	-5.5	A
Peak Pulse Current	I_{CM}	-15	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

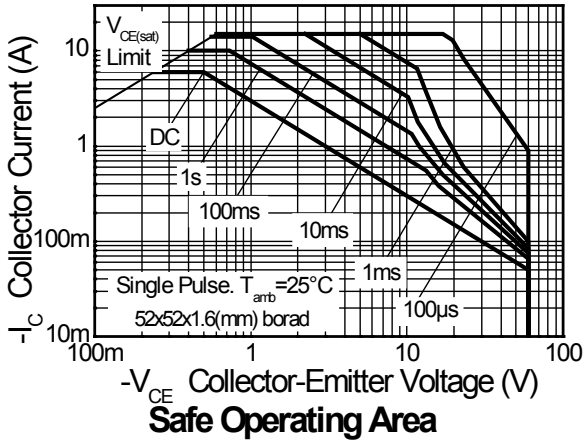
Characteristic		Symbol	Value	Unit
Power Dissipation Linear Derating Factor	(Note 5)	P_D	3.0 24	W mW/°C
	(Note 6)		1.6 12.8	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	42	°C/W
	(Note 6)	$R_{\theta JA}$	78	
Thermal Resistance Junction to Lead	(Note 7)	$R_{\theta JL}$	12.3	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

ESD Ratings (Note 8)

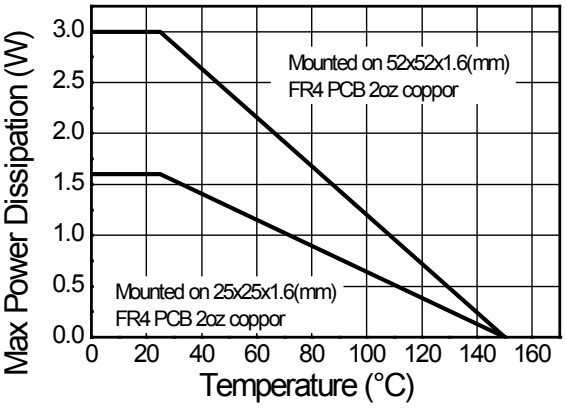
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

Notes:
5. For a device mounted with the collector lead on 52mm × 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
6. Same as Note 6, except the device is mounted on 25mm × 25mm 1oz copper.
7. Thermal resistance from junction to solder-point (at the end of the collector lead).
8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

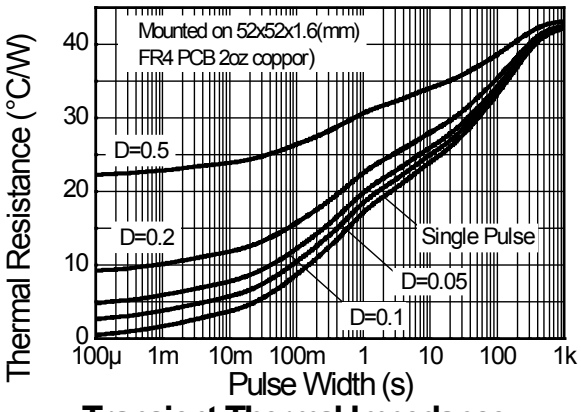
Thermal Characteristics



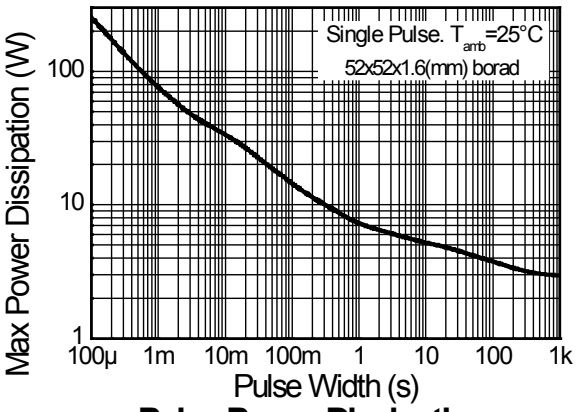
Safe Operating Area



Derating Curve



Transient Thermal Impedance



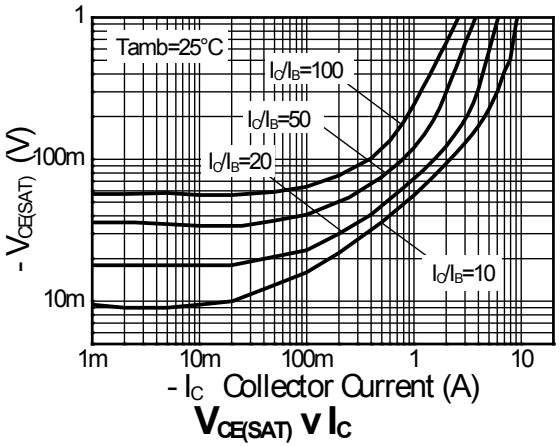
Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

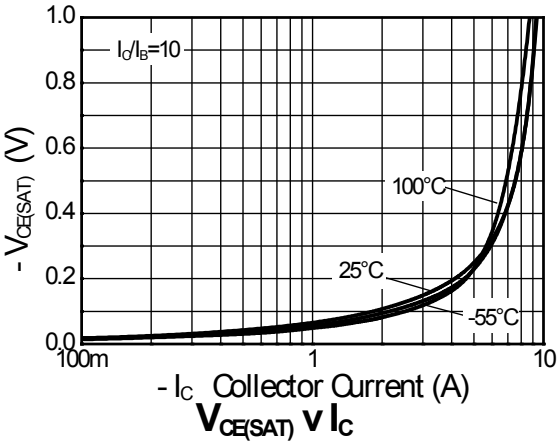
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	-90	-120	—	V	I_C = -100μA
Collector-Emitter Breakdown Voltage	BV_{CES}	-90	-120	—	V	I_C = -100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV_{CEO}	-60	-80	—	V	I_C = -10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	-8	—	V	I_E = -100μA
Collector-Base Cut-Off Current	I_{CBO}	—	-1	-50	nA	V_{CB} = -72V
Collector-Emitter Cut-Off Current	I_{CES}	—	-1	-50	nA	V_{CB} = -72V
Emitter Cutoff Current	I_{EBO}	—	-1	-10	nA	V_{EB} = -6V
Static Forward Current Transfer Ratio (Note 9)	h_{FE}	100	240	—	—	I_C = -10mA, V_{CE} = -2V
		100	180	300		I_C = -2A, V_{CE} = -2V
		40	70	—		I_C = -5A, V_{CE} = -2V
		5	14	—		I_C = -10A, V_{CE} = -2V
Collector-Emitter Saturation Voltage (Note 9)	$V_{CE(sat)}$	—	-16	-30	mV	I_C = -100mA, I_B = -10mA
		—	-55	-95		I_C = -1A, I_B = -100mA
		—	-85	-130		I_C = -2A, I_B = -200mA
		—	-200	-260		I_C = -5A, I_B = -500mA
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(sat)}$	—	-1	-1.15	V	I_C = -5A, I_B = -500mV
Base-Emitter Turn-On Voltage (Note 9)	$V_{BE(on)}$	—	-0.89	-1.0	V	I_C = -5A, V_{CE} = -2V
Output Capacitance (Note 9)	C_{obo}	—	33	70	pF	V_{CB} = -10V. f = 1MHz
Transition Frequency	f_T	—	120	—	MHz	V_{CE} = -10V, I_C = -100mA f = 50MHz
Switching Time	t_{on}	—	33	80	ns	V_{CC} = -10V, I_C = -2A
	t_{off}	—	215	300		I_{B1} = -I_{B2} = -200mA

Note: 9. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

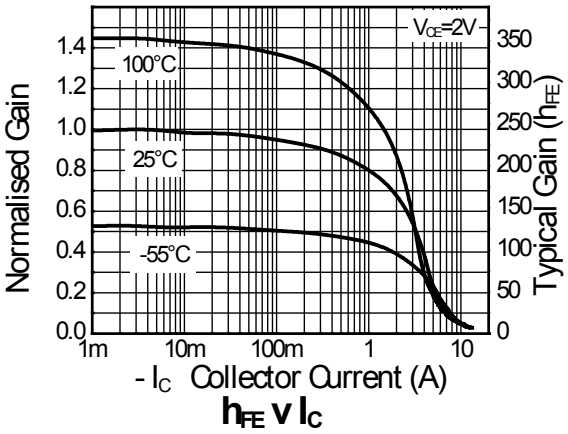
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



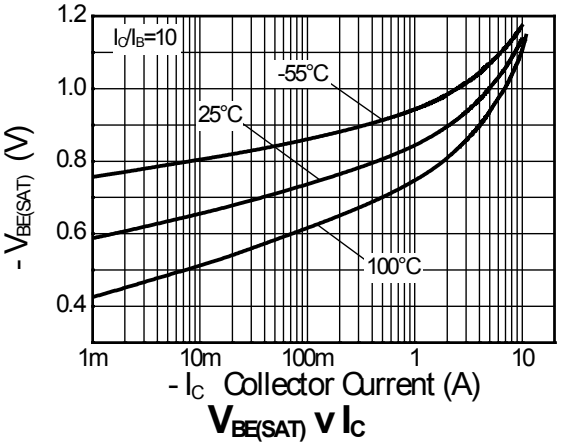
$V_{CE(SAT)}$ v I_C



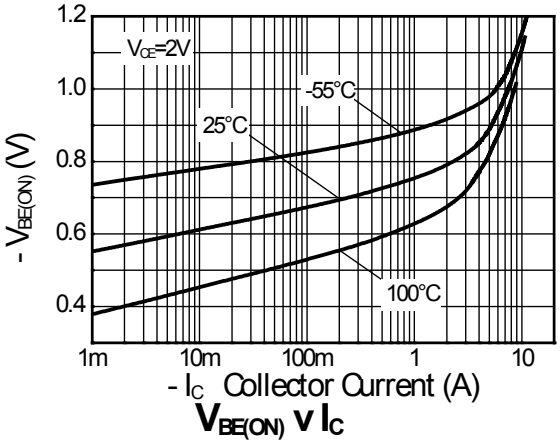
$V_{CE(SAT)}$ v I_C



h_{FE} v I_C



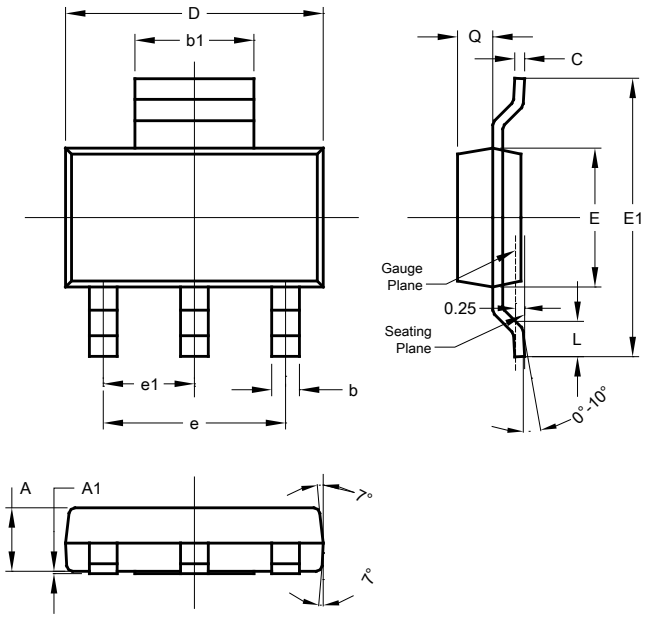
$V_{BE(SAT)}$ v I_C



$V_{BE(ON)}$ v I_C

Package Outline Dimensions

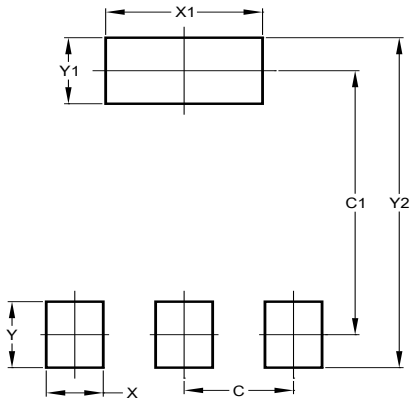
SOT223



SOT223			
Dim	**Min**	**Max**	**Typ**
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout

SOT223



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00